

0.5A Low V_F Schottky Barrier Rectifier

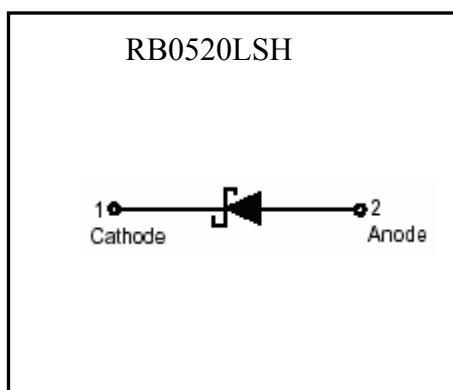
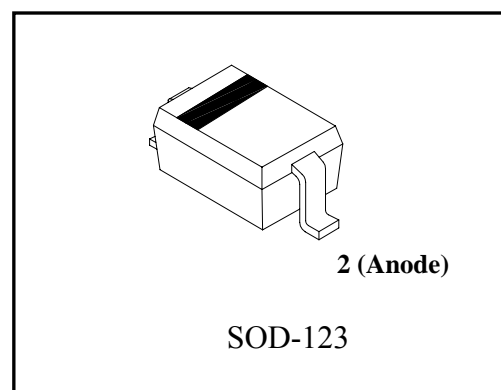
RB0520LSH

Features

- High current capability, low forward voltage drop
- High surge current capability
- Low power loss, high efficiency
- High temperature soldering guaranteed, 250°C/10 seconds
- Low profile surface mounted package in order to minimize board space
- Pb-free lead plating and halogen-free package

Mechanical data

- Case : Molded plastic, JEDEC SOD-123.
- Epoxy : UL94-V0 rated flame retardant
- Terminals : Plated terminals, solderable per MIL-STD-202 method 208
- Polarity : Indicated by cathode band
- Mounting position : Any
- Weight : approx. 0.04 gram

Symbol**Outline**

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameters	Conditions	Symbol	Min	Typ	Max	Units
Repetitive peak reverse voltage		V_{RRM}			20	V
RMS voltage		V_{RMS}			14	V
Continuous reverse voltage		V_R			20	V
Forward rectified current		I_O			0.5	A
Forward surge current	8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}			10	A
Thermal resistance	Junction to Case	$R_{\theta JC}$		200		$^{\circ}\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$		250		
Storage temperature range		T_{stg}	-65		150	$^{\circ}\text{C}$
Operating junction temperature range		T_j	-55		125	$^{\circ}\text{C}$

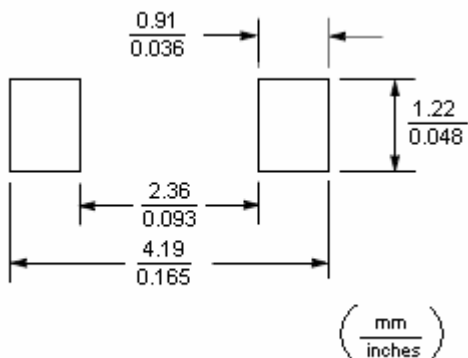
Characteristics ($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Condition	Min.	Typ	Max.	Unit
	V_R	$I_R=200\mu\text{A}$	20	-	-	V
Forward Voltage	$V_F 1$	$I_F=100\text{mA}$	-	-	300	mV
	$V_F 2$	$I_F=500\text{mA}$	-	-	385	
Reverse Leakage Current	$I_R 1$	$V_R=10\text{V}$	-	-	100	μA
	$I_R 2$	$V_R=20\text{V}$	-	-	200	μA
Junction Capacitance	C_J	$V_R=4\text{V}, f=1\text{MHz}$	-	36	-	pF

Ordering Information

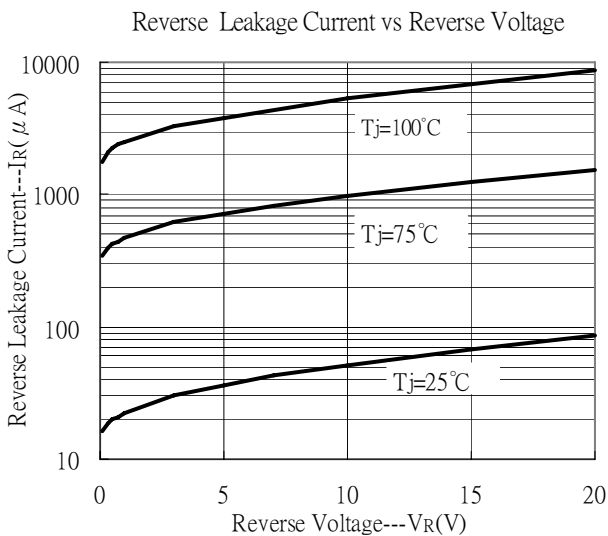
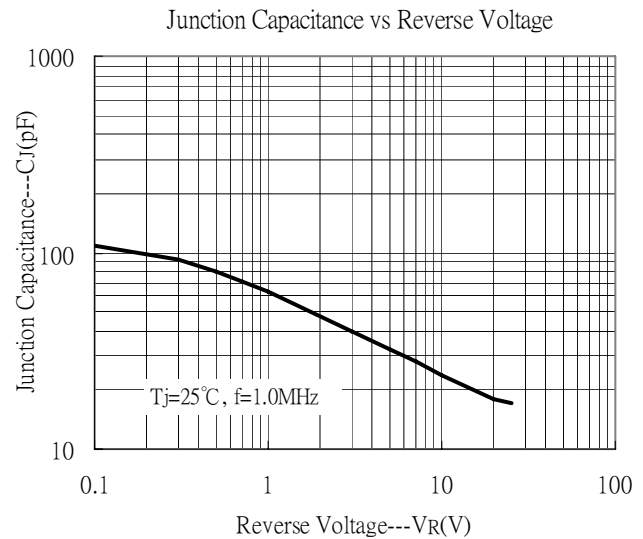
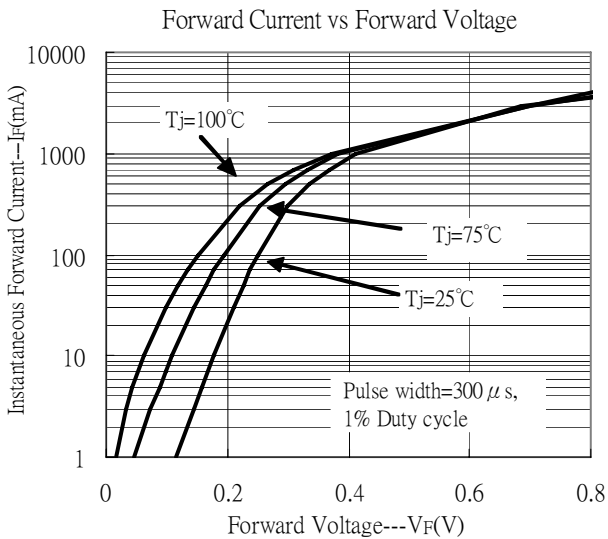
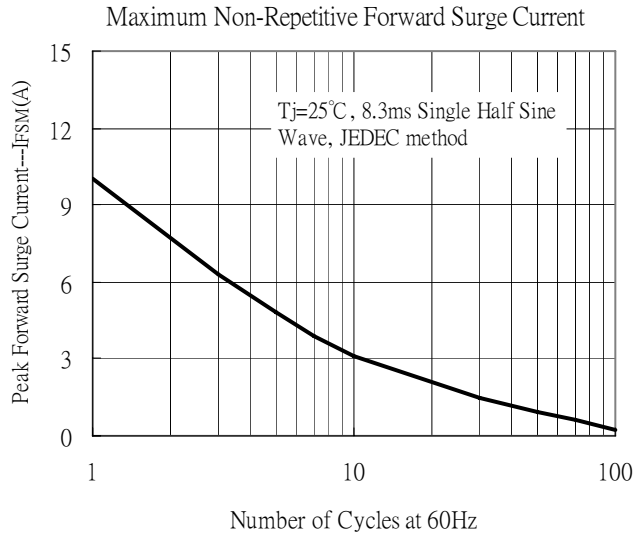
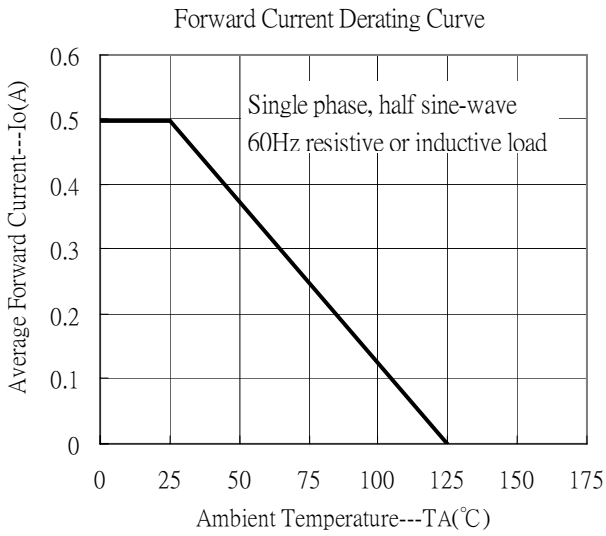
Device	Package	Shipping
RB0520LSH-0-T1-G	SOD-123 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Recommended Soldering Footprint

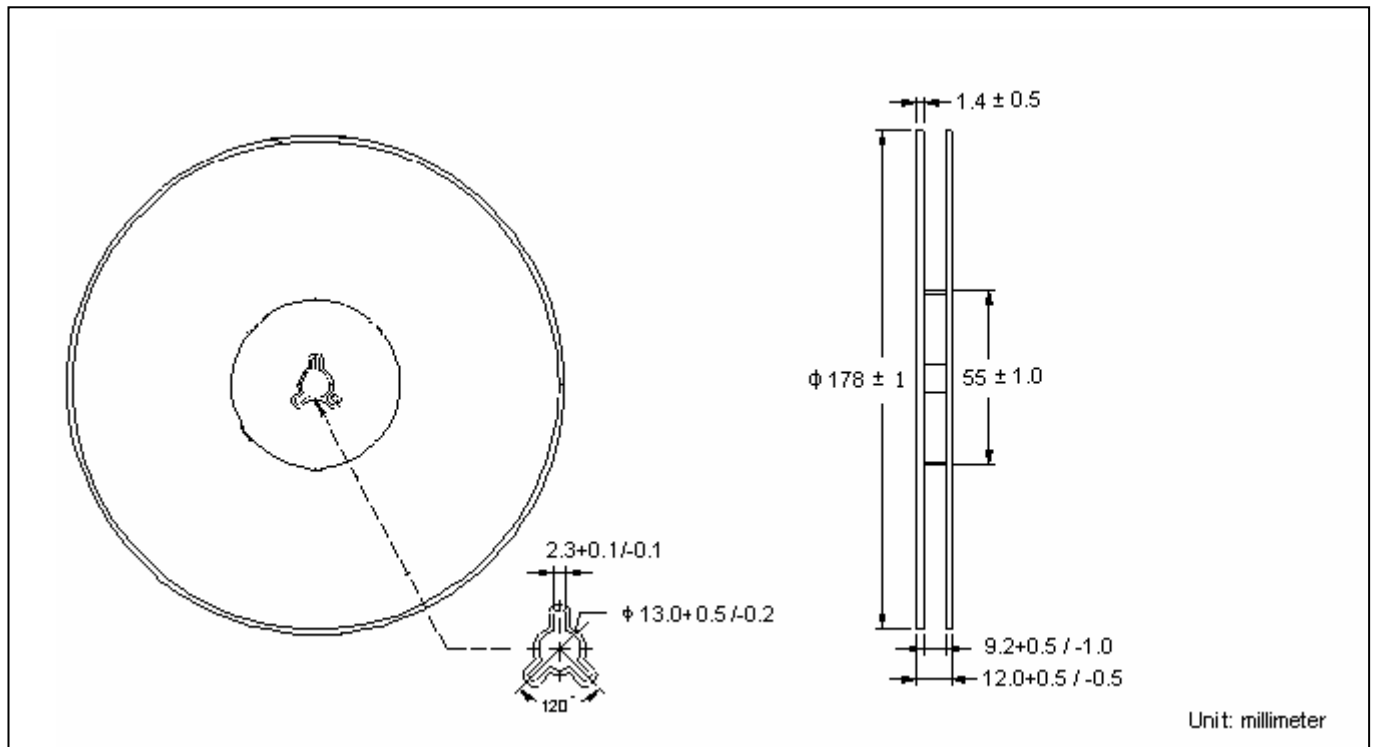




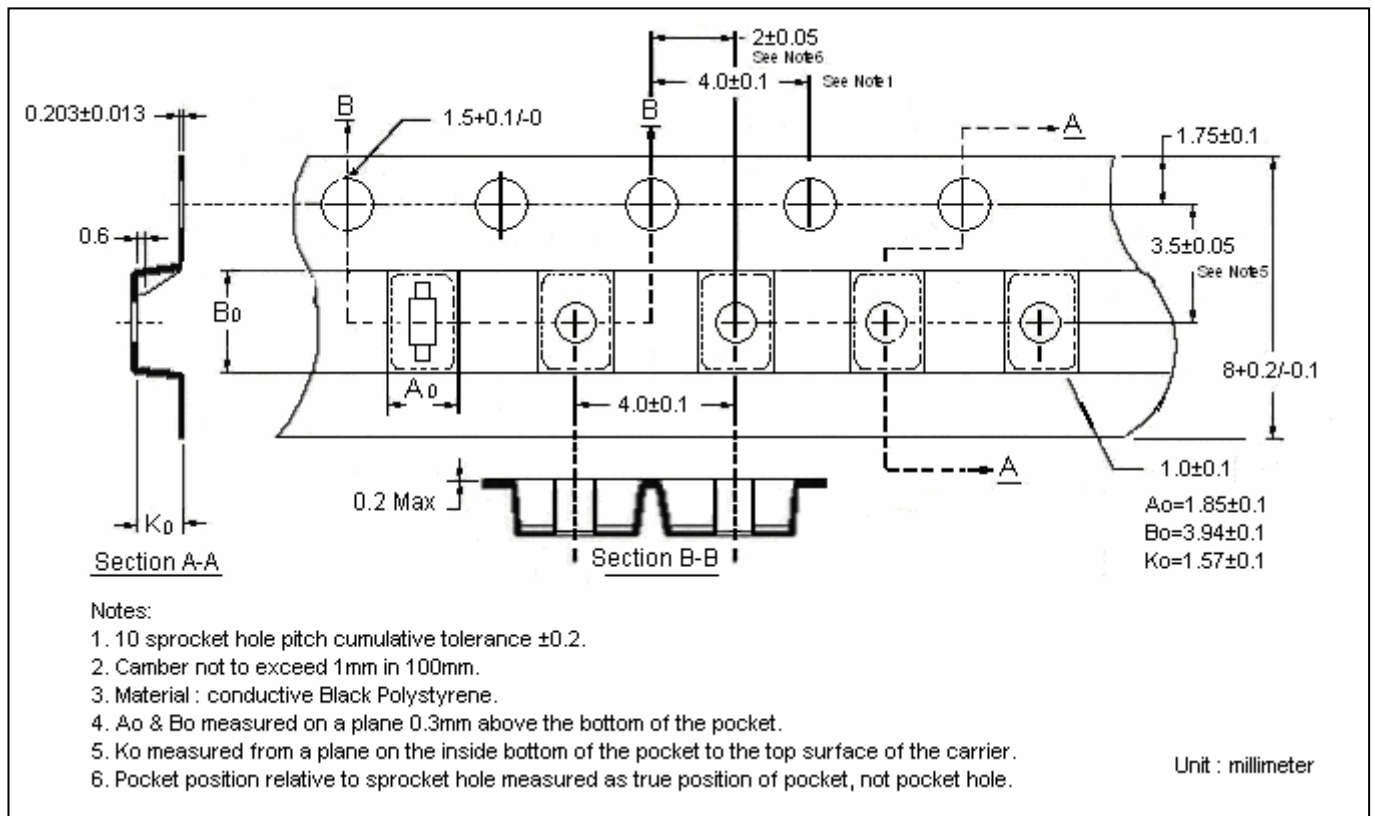
Characteristic Curves



Reel Dimension



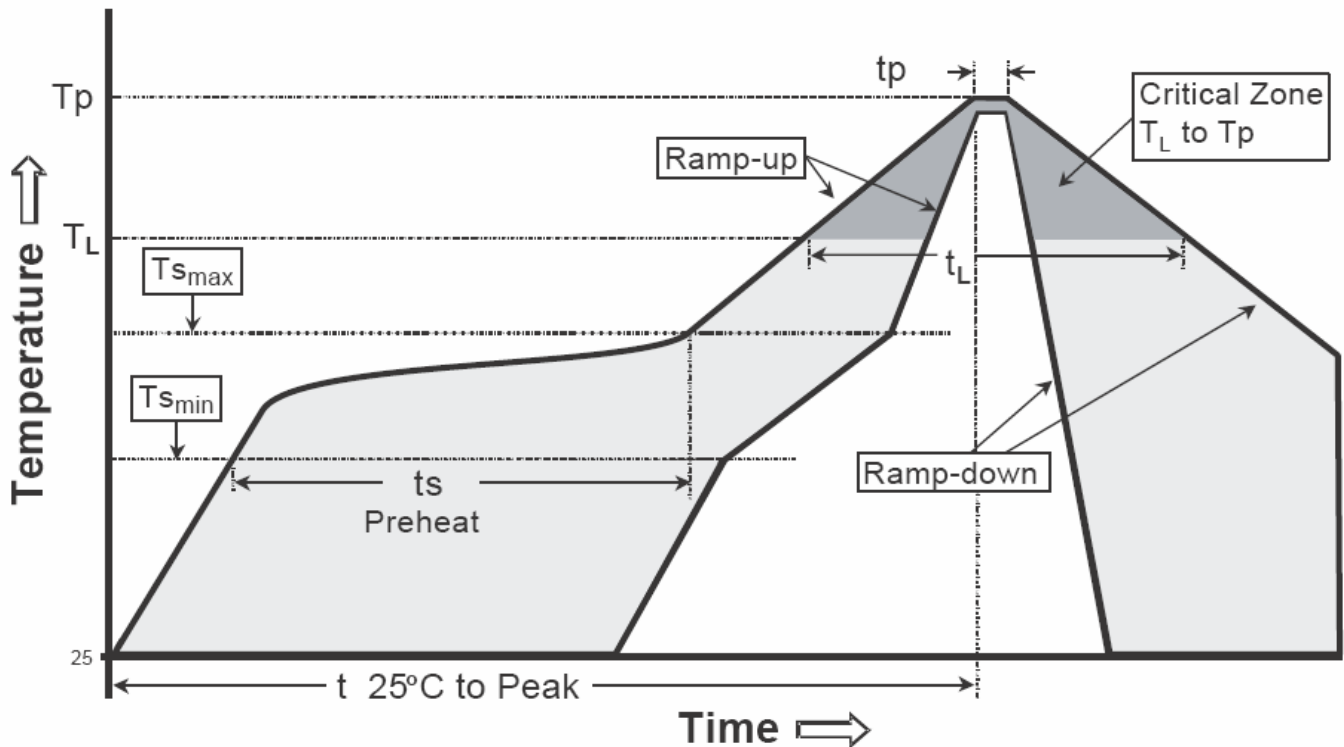
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

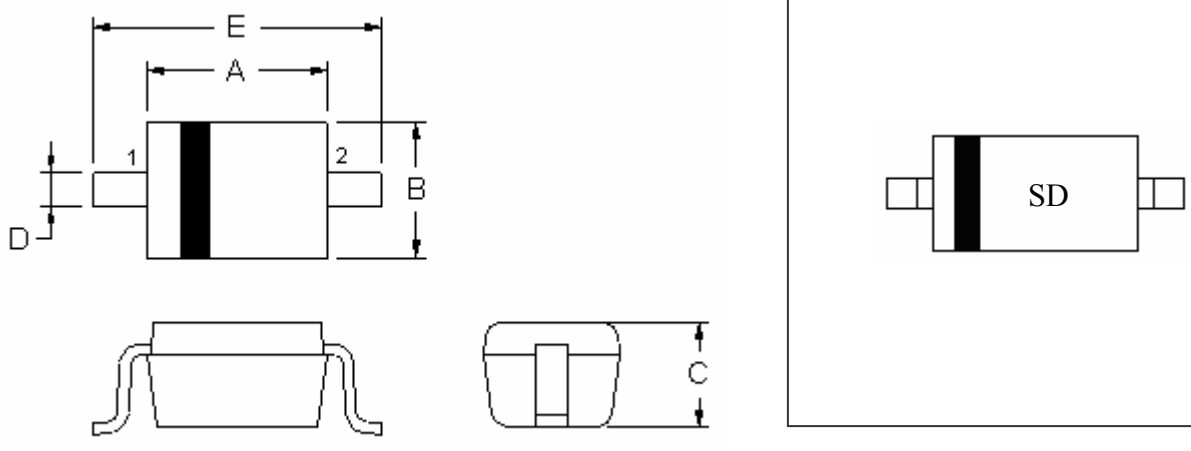
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOD-123 Dimension



2-Lead SOD-123 Plastic
 Surface Mounted Package
 CYStek Package Code: SH

Style: Pin 1.Cathode 2.Anode

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.102	0.110	2.600	2.800	D	0.018	0.026	0.450	0.650
B	0.059	0.067	1.500	1.700	E	0.140	0.152	3.550	3.850
C	0.041	0.049	1.050	1.250					

Notes: 1.Controlling dimension : millimeters.
 2.Lead thickness specified per L/F drawing with solder plating.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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